

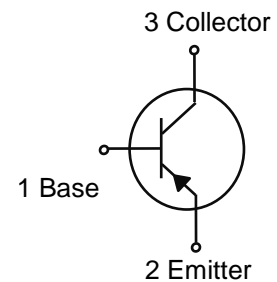
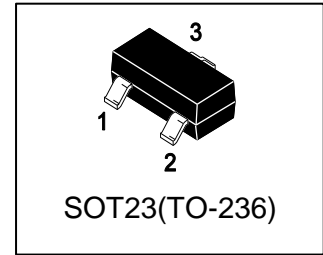
LMBTA94LT1G

S-LMBTA94LT1G

PNP EPITAXIAL PLANAR TRANSISTOR

1. FEATURES

- High Breakdown Voltage.
- We declare that the material of product compliance with RoHS requirements and Halogen Free.
- S-prefix for automotive and other applications requiring unique site and control change requirements; AEC-Q101 qualified and PPAP capable.



2. DEVICE MARKING AND ORDERING INFORMATION

Device	Marking	Shipping
LMBTA94LT1G	4Z	3000/Tape&Reel

3. MAXIMUM RATINGS(Ta = 25°C)

Parameter	Symbol	Limits	Unit
Collector–Emitter Voltage	VCEO	-400	V
Collector–Base Voltage	VCBO	-400	V
Emitter–Base Voltage	VEBO	-6	V
Collector Current — Continuous	IC	-150	mA

4. THERMAL CHARACTERISTICS

Parameter	Symbol	Limits	Unit
Total Device Dissipation, FR-5 Board (Note 1) @ TA = 25°C Derate above 25°C	PD	225 1.8	mW mW/°C
Thermal Resistance, Junction–to–Ambient	RθJA	556	°C/W
Total Device Dissipation, Alumina Substrate (Note 2) @ TA = 25°C Derate above 25°C	PD	300 2.4	mW mW/°C
Thermal Resistance, Junction–to–Ambient	RθJA	417	°C/W
Junction and Storage Temperature	TJ,Tstg	-55 ~ +150	°C

1. FR-5 = 1.0 x 0.75 x 0.062 in.

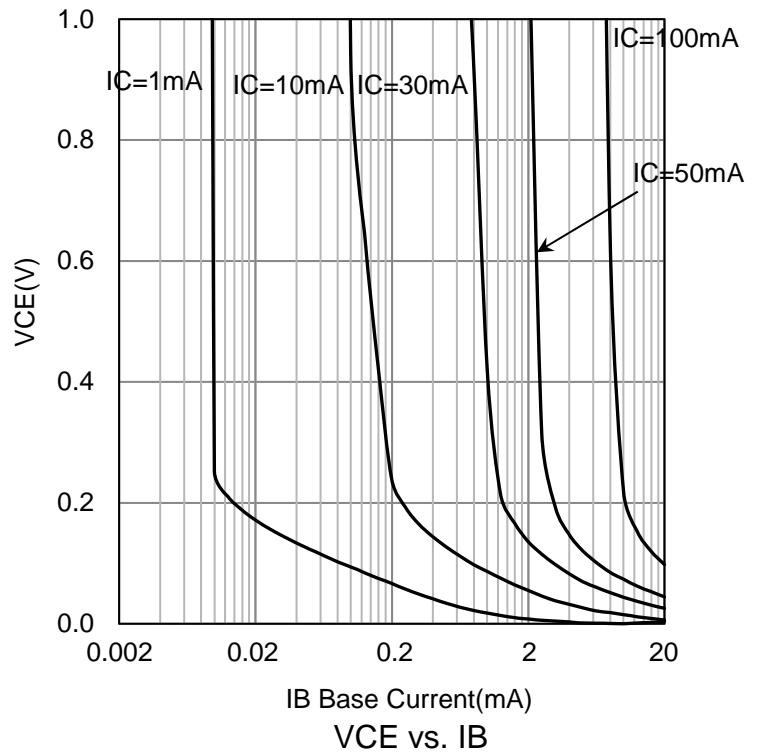
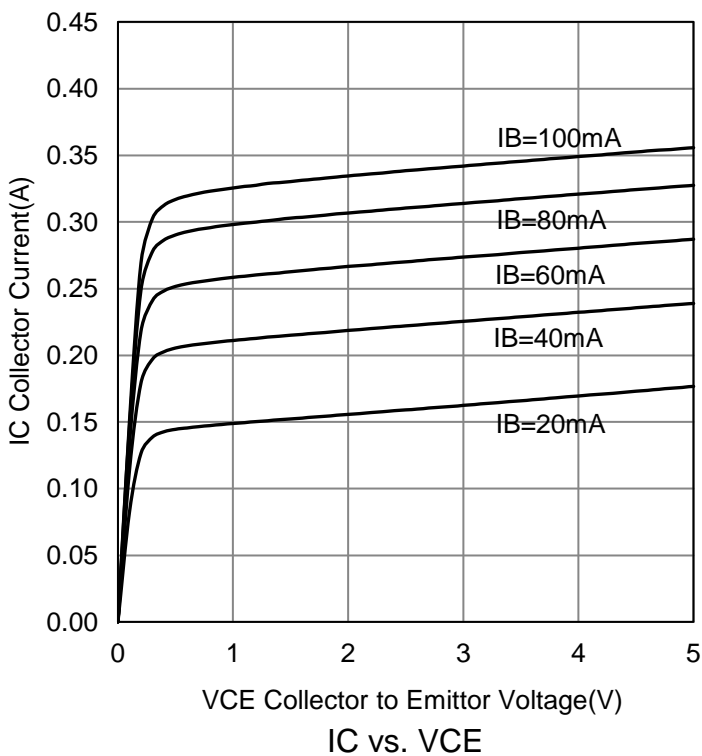
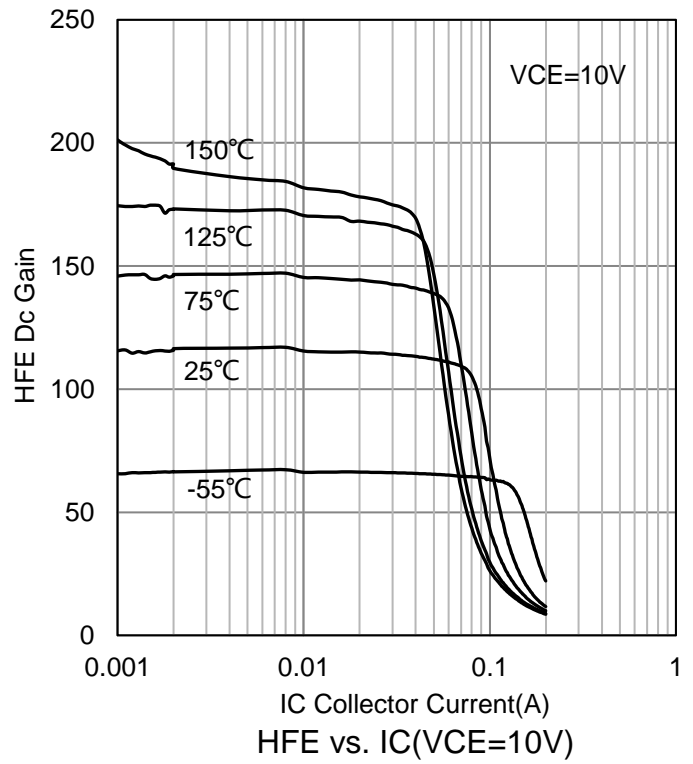
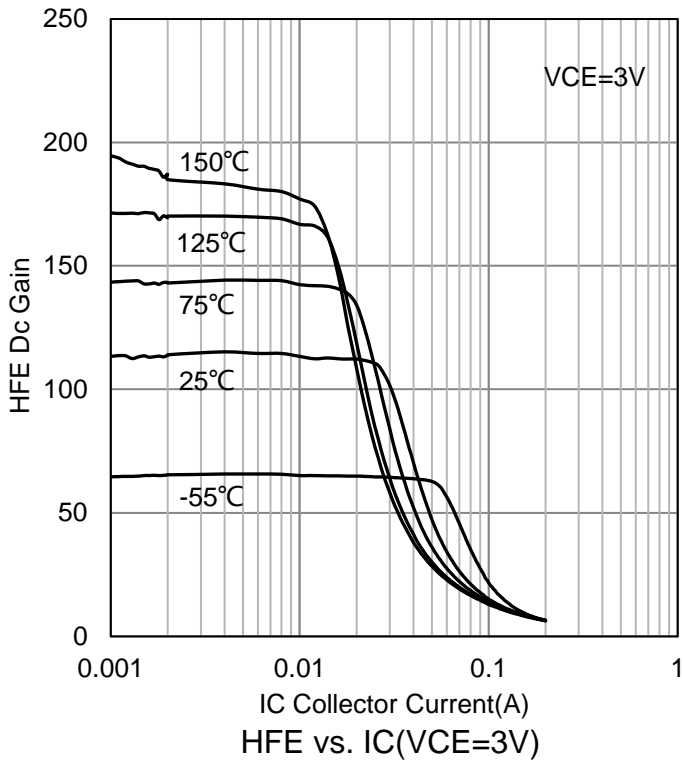
2. Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.

5. ELECTRICAL CHARACTERISTICS (Ta= 25°C)

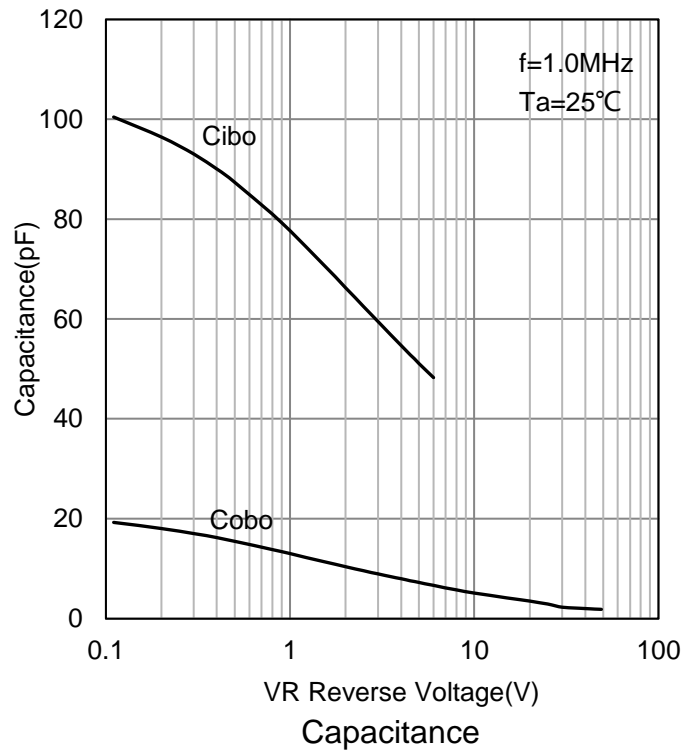
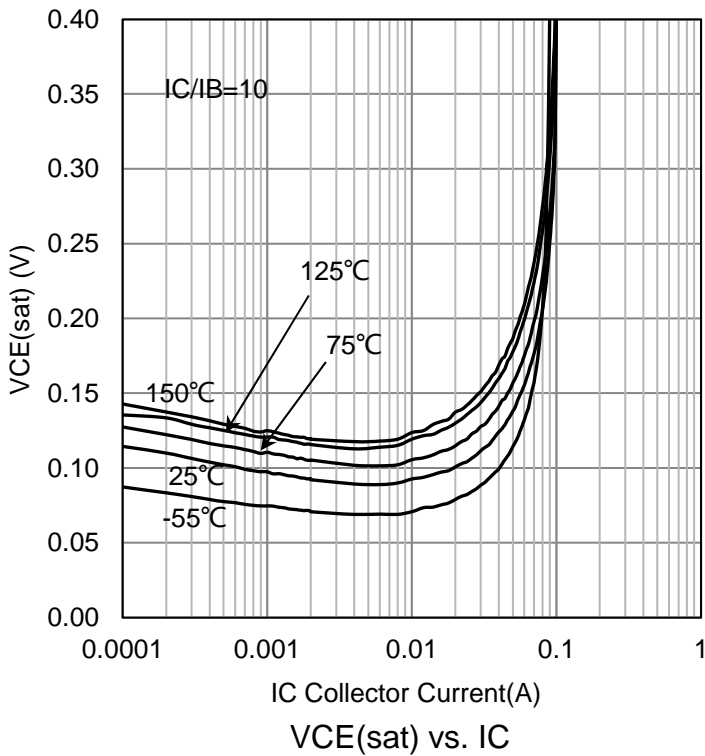
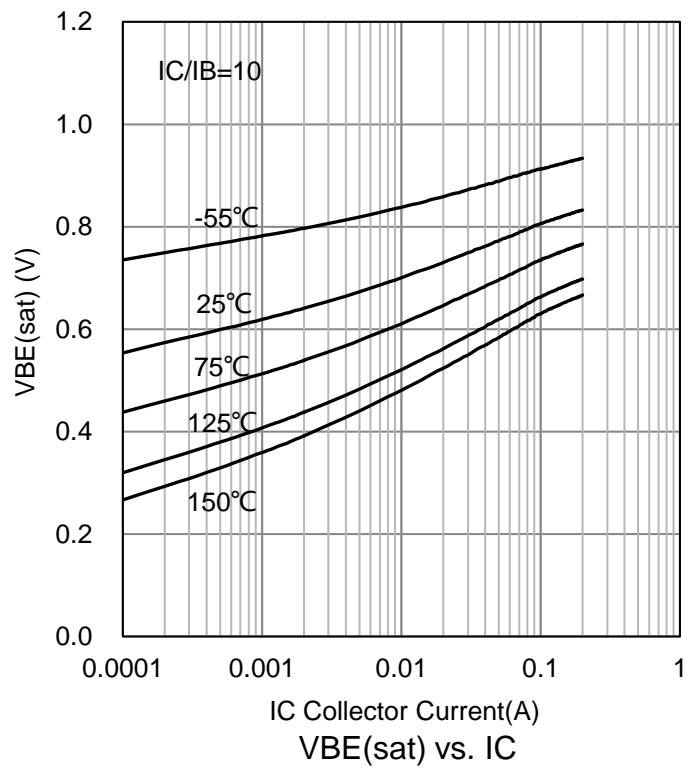
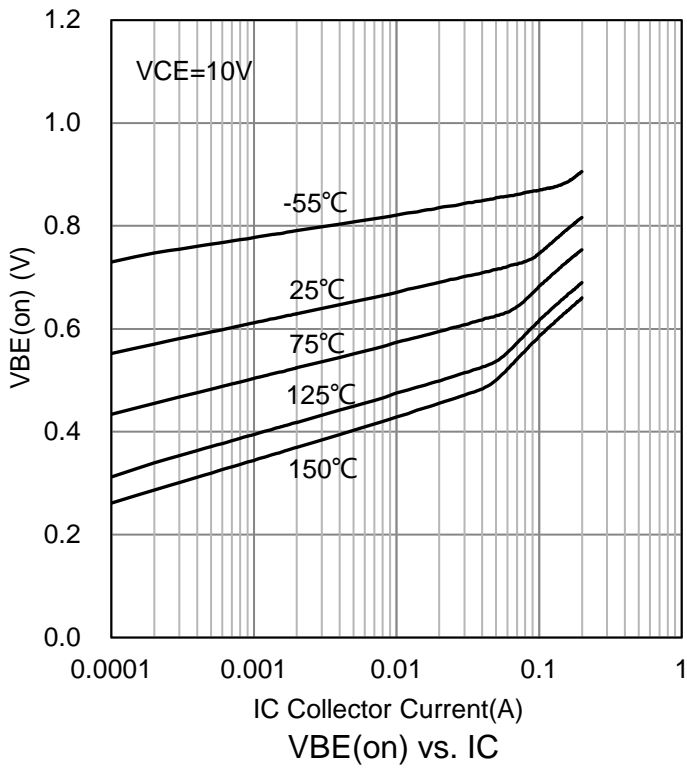
Characteristic	Symbol	Min.	Typ.	Max.	Unit
Collector–Emitter Breakdown Voltage(Note 2) (IC = -1 mA, IB = 0)	VBR(CEO)	-400	-	-	V
Collector–Emitter Breakdown Voltage (IC = -100 μA, IE = 0)	V(BR)CBO	-400	-	-	V
Emitter–Base Breakdown Voltage (IE = -10 μA, IC = 0)	VBR(EBO)	-6	-	-	V
Collector-Base Cutoff Current (VCB = -400V, IE = 0)	ICBO	-	-	-100	nA
Emitter-Base Cutoff Current (VEB = -6.0V, IC = 0)	IEBO	-	-	-100	nA
Collector Cutoff Current (VCE = -400V, VBE=0)	ICES	-	-	-500	nA
DC Current Gain (VCE=-10V, IC=-1mA) (VCE=-10V, IC=-10mA) (VCE=-10V, IC=-50mA) (VCE=-10V, IC=-100mA)	HFE	50 75 60 20	- - - -	- 200 - -	
Collector–Emitter Saturation Voltage (IC = -1mA, IB= -0.1mA) (IC = -10mA, IB= -1mA) (IC = -50mA, IB= -5mA)	VCE(sat)	- - -	- - -	-200 -300 -600	mV
Base–Emitter Saturation Voltage (IC=-10mA, IB=-1mA)	VBE(sat)	-	-	-900	mV
Collector Capacitance (VCB = -10 V, f = 1.0 MHz)	Cob	-	4	6	pF

 1. Pulse Test: Pulse Width $\leq 300 \mu\text{s}$, Duty Cycle $\leq 2.0\%$.

6.ELECTRICAL CHARACTERISTICS CURVES



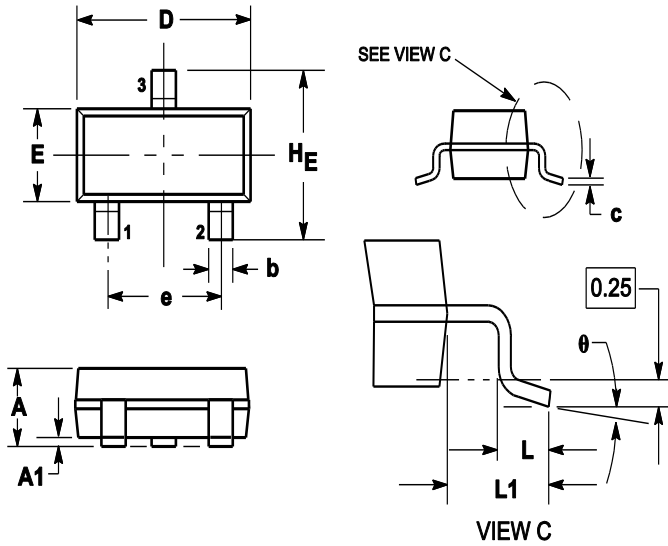
6.ELECTRICAL CHARACTERISTICS CURVES(Con.)



7. OUTLINE AND DIMENSIONS

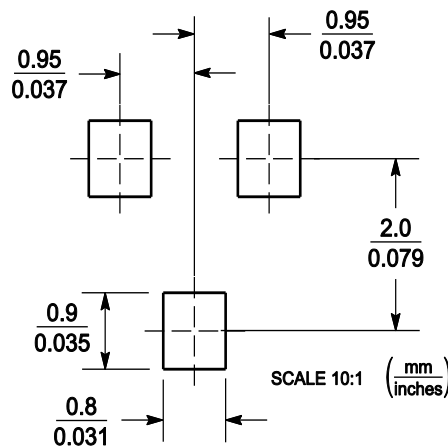
Notes:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.



DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.89	1	1.11	0.035	0.04	0.044
A1	0.01	0.06	0.1	0.001	0.002	0.004
b	0.37	0.44	0.5	0.015	0.018	0.02
c	0.09	0.13	0.18	0.003	0.005	0.007
D	2.80	2.9	3.04	0.11	0.114	0.12
E	1.20	1.3	1.4	0.047	0.051	0.055
e	1.78	1.9	2.04	0.07	0.075	0.081
L	0.10	0.2	0.3	0.004	0.008	0.012
L1	0.35	0.54	0.69	0.014	0.021	0.029
HE	2.10	2.4	2.64	0.083	0.094	0.104
θ	0°	---	10°	0°	---	10°

8. SOLDERING FOOTPRINT



DISCLAIMER

- Curve guarantee in the specification. The curve of test items with electric parameter is used as quality guarantee. The curve of test items without electric parameter is used as reference only.
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